SC DETECTION CIRCUIT

NIPUN KAUSHIK

OUTLINE

- I. Side Channel Attacks (SCA) Countermeasures to detection
- 2. Power Side Channel Attack (PSCA) and threat model
- 3. System and Circuit design
 - I. First Tapeout (July 2021)
 - 2. Second Tapeout (July 2022)
 - 3. Simulation Results
- 4. Results

SIDE CHANNEL ATTACKS

- Threat to devices handling sensitive information (Smart cards, servers, AES, DES, etc.)
- Countermeasure against SCA work towards making the device robust to against side channel attacks [1-4]
- Detection circuits for power side channel attacks (P-SCA) focus on detection of an attack in real time machine learning [5]-[6], Ring oscillator [7]
- Detection circuit can be improve by decreasing the number of required sensors, sensing the resistor insertion at PCB level.

POWER SIDE CHANNEL ATTACKS (PSCA) AND THREAT MODEL

How is a P-SCA conducted?

- 1. Insertion of a sense resistor in the power supply of the device.
- 2. Send plain text to the device
- 3. Collect large number of traces during encryption process
- 4. Use statistical methods to extract the secret key.
- 5. Statistical operation include Differential Power Analysis (DPA), Correlational Power Analysis (CPA) etc.

THREAT MODEL

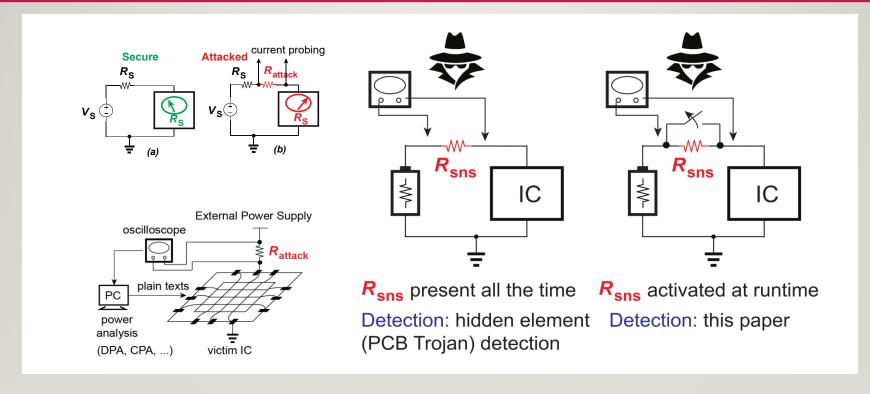
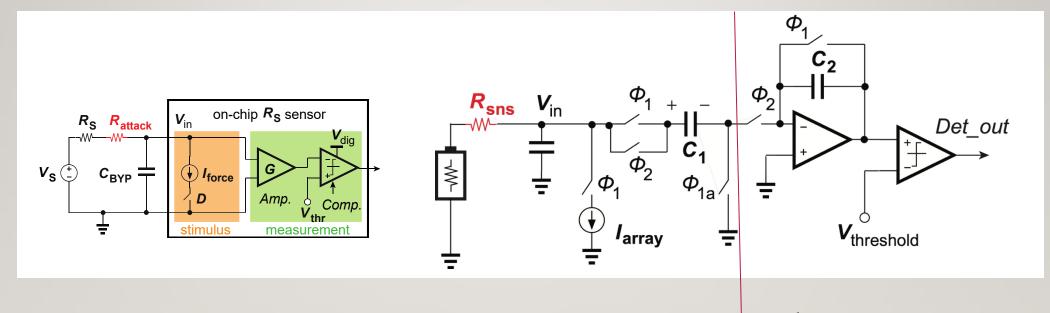


Fig 1:Threat model

SYSTEM LEVEL DESIGN & CIRCUIT TOPOLOGY

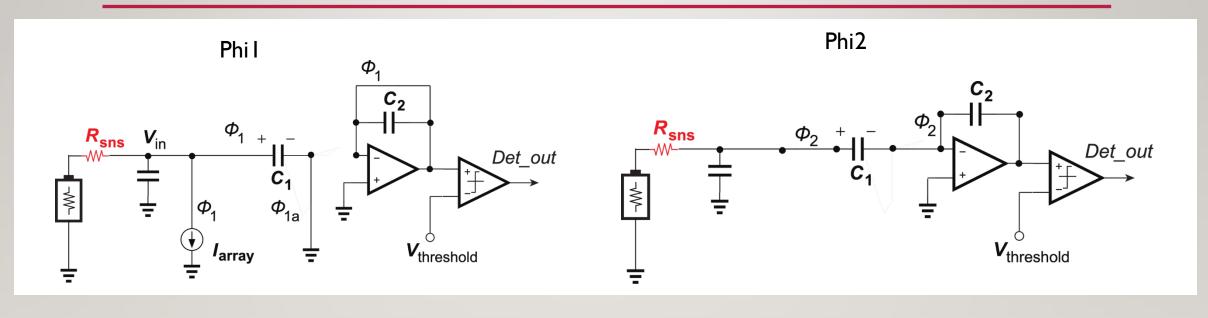


3.3V direct interface I/O domain

1V low power energy efficient domain

Fig 2: System and Circuit topology

PHI1 AND PHI2 FOR SC CIRCUIT



$$Q_x = -(I_{array}. R_{sense})(n). C_1$$
 $Q_x = -V_{out}(n + 1/2). C_2$

Fig 3: Circuit operation in different phases

METRICS

Sampling rate = 200KHz

Charge redistribution and conversion

$$-V_{in}C_1 = -Vout\left(n + \frac{1}{2}\right)C_2$$

Output is a scaled and delayed version of input

$$V_{out}\left(n+\frac{1}{2}\right)=\frac{c_1}{c_2}.V_{in}(n)$$

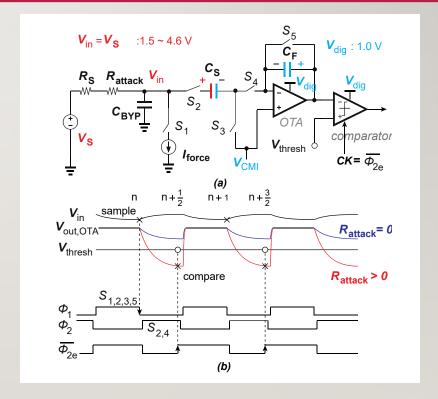
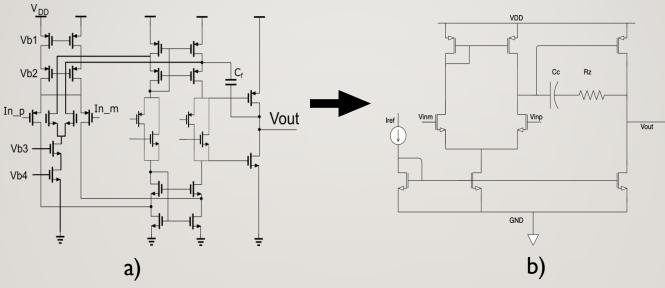


Fig 4: Sensing operation a) Circuit configuration b) Timing waveform

AMPLIFIER



 $Gain = (gm_n + gm_p)R_{ocas}.(gm_n + gm_p)R_{out}$

Trade speed with power efficiency, keep gain similar

Bandwidth = 16MHz with PM 89°

Figure 5: Operational amplifier used in SC amplifier a) Folded Cascode b) Two-stage OTA

COMPARATOR

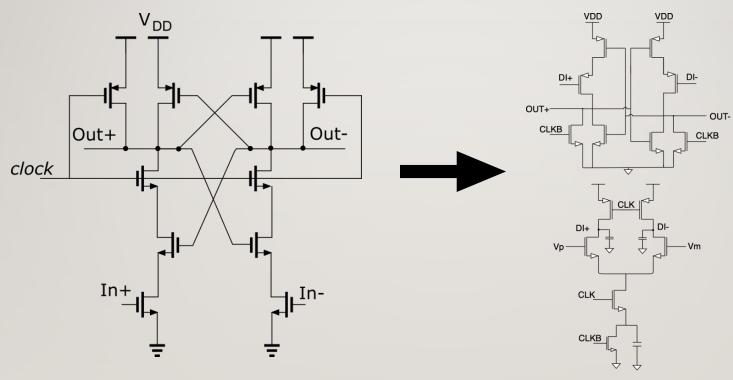


Fig 6: Strong arm clocked comparator, Baker. J [8]

Fig 7: Dynamic Bias comparator, Bindra H. [9]

RELATIONSHIP OF NOISE WITH CIRCUIT

According to normal Z distribution table;

The equation represents the following parameters:

 μ_0 = Threshold without sense resistor R_{sns}

 μ_1 = Threshold with sense resistor R_{sns}

 R_{sns} = Sense resistor

 σ = Total noise distribution

G = Gain of the track and hold circuit

 I_{array} = Excitation current used in the system

$$\overline{\sigma^2} = \overline{\sigma_{THA}^2} + \overline{\sigma_{comp}^2}$$

$$\mu_0 = G \cdot \Delta V = G \cdot I_{array} R_S$$

$$\mu_1 = G \cdot \Delta V' = G \cdot I_{array}(R_S + R_{sns})$$

$$\mu_0 - \mu_1 \ge 2 \times 1.645 \sigma = 3.29 \sigma$$

$$R_{sns} \ge \frac{3.29\sigma}{G.I_{array}}$$

NOISE ANALYSIS

• $f(\alpha, \beta)$ for 95% confidence level = 3.29

$$\sigma = \sqrt{G^2 \sigma_{THA,in}^2 + \sigma_{comp}^2}$$

 $R_{SNS,min} = \frac{f(\alpha, \beta)}{I_{array}} \sqrt{\sigma_{THA,in}^2 + \frac{\sigma_{comp}^2}{G^2}}$

- $I_{array} 100 = \mu A$
- Total noise distribution from SC circuit
- and comparator $\sigma = 1.07 \text{mV}$
- Gain of the track and hold circuit G = 30 We get $R_{sns} \ge \frac{3.29 \times 33 \mu V}{100 \mu} A = 1.08 \Omega$

RESULTS

TYPICAL CORNER SIMULATION – 1ST ITERATION

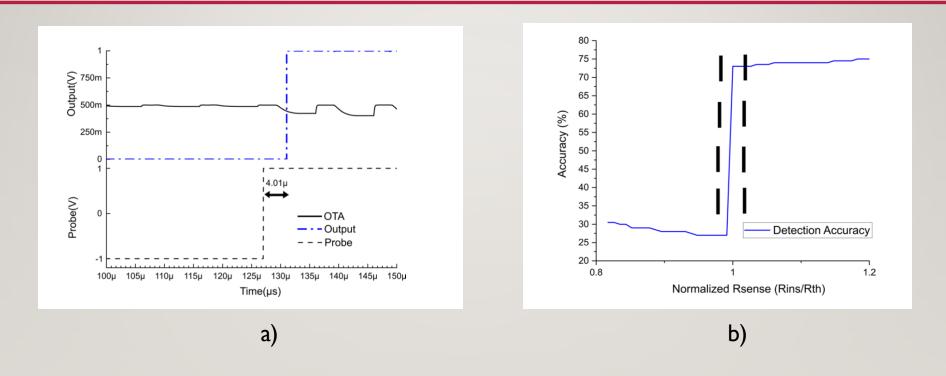


Fig 8: a) Detection time and b) Detection accuracy

AFTER NOISE ANALYSIS— 2ND ITERATION

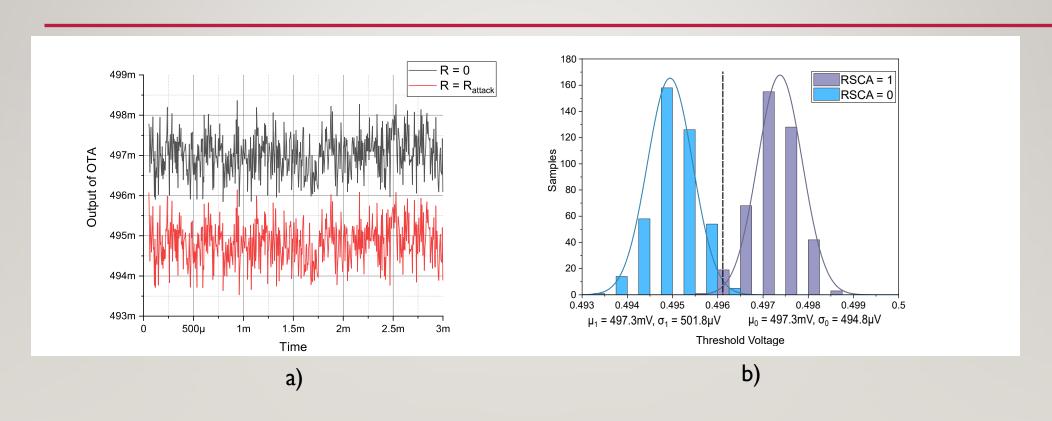
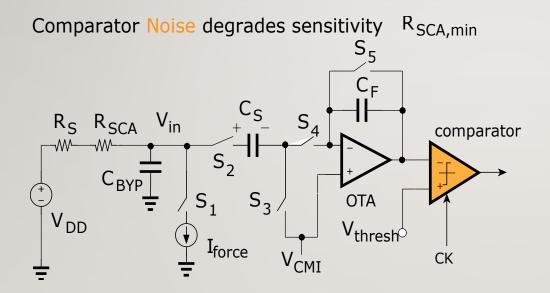


Fig 9: a) Transient Noise at the output of OTA and b) Noise distribution at the output of OTA

COMPARATOR NOISE



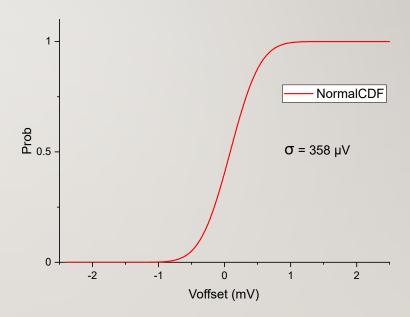


Fig 10: Comparator Noise performance

TAPEOUT 1

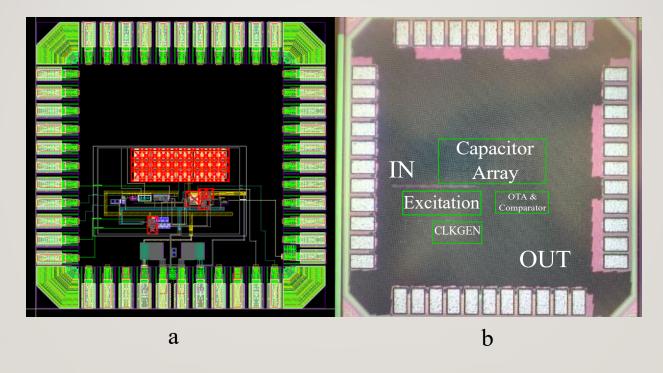


Fig II:a) Chip layout in the simulator b) Die photo

BONDING DIAGRAM

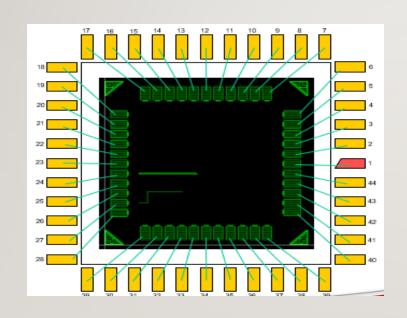




Fig 12: 40 pin CLCC package for the first iteration

PCB DESIGN

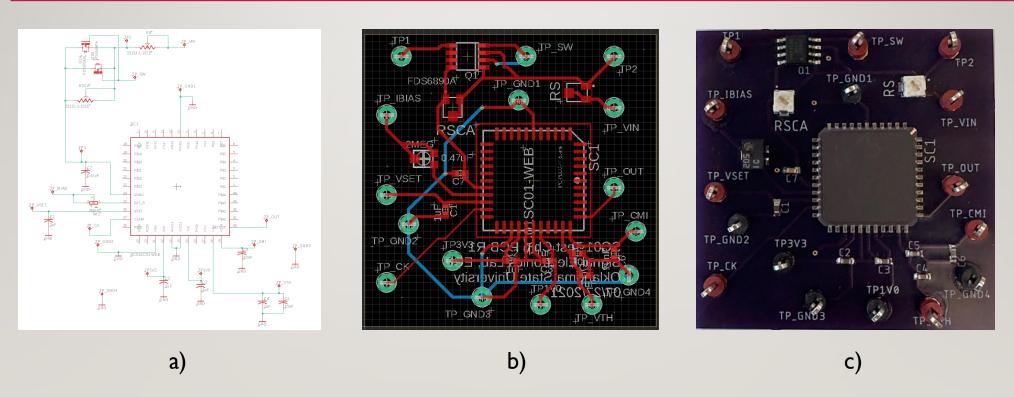


Fig 13: PCB design for test chip in EAGLE a) Schematic b) Board layout c) Fabricated board

RESULT

- PCB designed, signal at the input, and the tunable current array works.
- An additional latch at the end of the comparator output caused the problem at the output.
- Noise is a problem; can we use data-driven noise reduction to further improve performance?

LEARNINGS FROM FAILURE - 1

- Create test modes to test various points in the chip Created test modes for second tapeout
- Removed the latch at the end to resolve the ESD problem.
- Investigate DDNR for the second tapeout, add a digital block to take more than one sample, and improve the confidence level. This can reduce false positive detection.

DATA DRIVEN NOISE REDUCTION

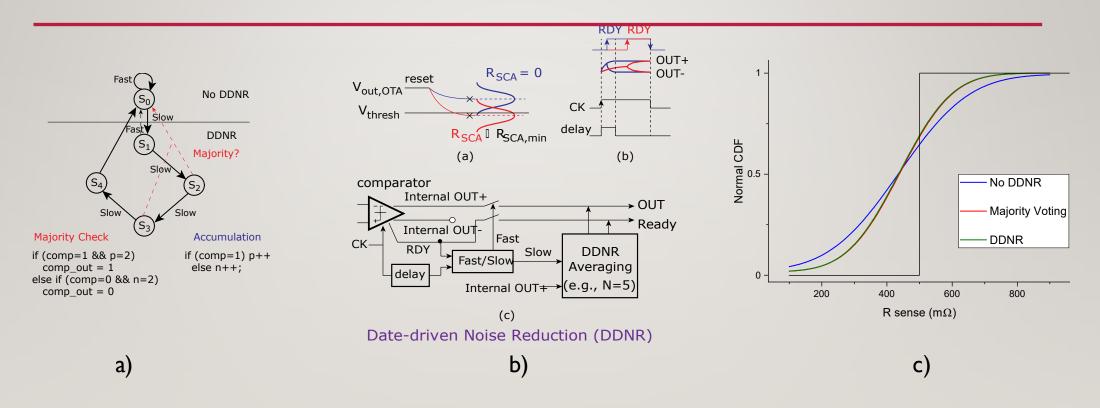


Fig 14: Finite state machine for DDNR b) System level update c) Comparison with majority voting scheme

DDNR SIMULATION RESULT

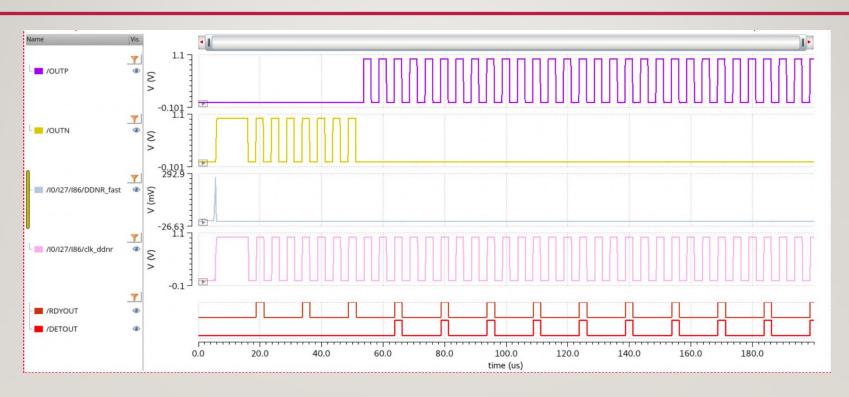
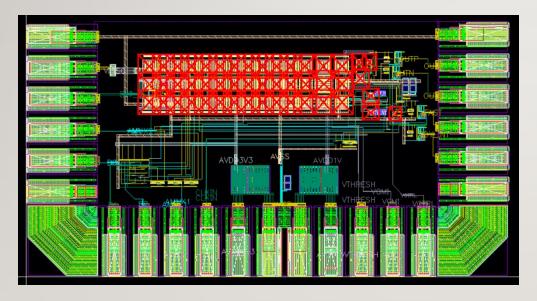
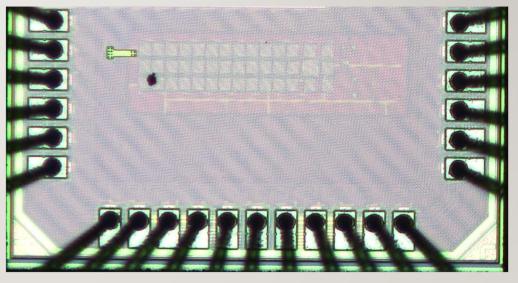


Fig 15: Simulation result with digital DDNR block

TAPEOUT 2





a) SC02 Chip Layout

b) Die photo

Fig 16: Second tapeout with corrections

PCB PLAN - 2

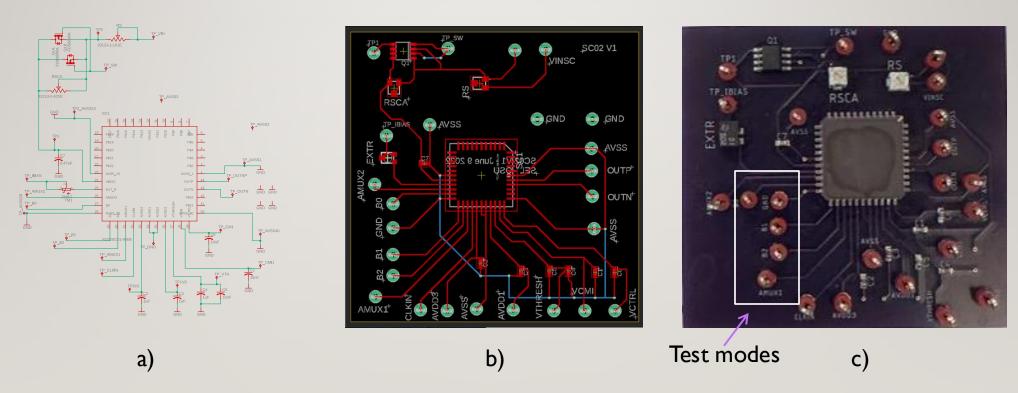


Fig 17: PCB for second chip a) Schematic b) Board layout c) Fabricated PCB

TESTMODES

Table 4: Test Mode Operation

B_2	B_1	B_0	Testmode	AMUX1	AMUX2	Goal
0	0	0	TM0	NC	NC	Normal operation
0	0	1	TM1	$V_{OUT,OTA}$	V_{C2}	Input/output of OTA accessible; external feedback on PCB
0	1	0	TM2	$V_{OUT,OTA}$	RDY_{INT}	$V_{OUT,OTA}$ in unity feedback; test comparator, $V_{CMI},$ and $V_{Threshold}$ accessible
0	1	1	TM3	$V_{OUT,OTA}$	Fast	Set Fast threshold; $V_{OUT,OTA}$ accessible
1	0	0	TM4	NC	Fast	Normal operation; observe Fast
1	0	1	TM5	NC	$Fast_{EXT}$	Fast accessible

Table 1: Table of test modes for the second iteration

MEASUREMENT AND CONCLUSION

- Duty cycling the current gives the expected waveform and values.
- The result couldn't be verified with DDNR due to a failure in detection.
- This concluded the project, and we proceeded to secure the conversion. PSCA analysis of secure ADC's.
- The associated journal submissions are available in the directory.

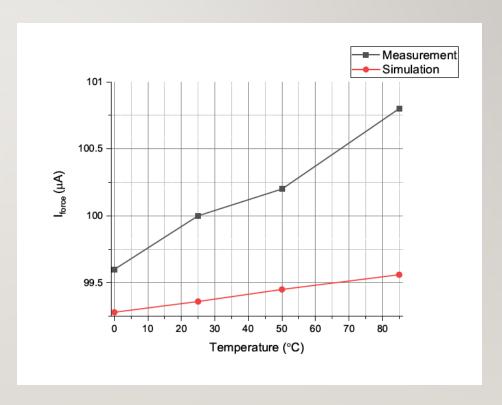


Fig 19: Iforce variation with Temperature

MEASUREMENT SETUP

Oscilloscope Battery current measurement

CLK OUTP OUTN

Clock source

Fig 18: Measurement setup for the board with sources and oscilloscope

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